

# April 1999 ADVANCE INFORMATION

# FDD6030BL

# N-Channel PowerTrench™ MOSFET

## **General Description**

This N-Channel Logic level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the onstate resistance and yet maintain low gate charge for superior switching performance.

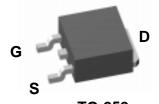
### **Applications**

- DC/DC converter
- Motor drives

### **Features**

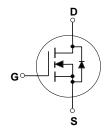
• 35 A, 30 V. 
$$R_{DS(ON)} = 0.018~\Omega~$$
 @  $V_{GS} = 10~V$  
$$R_{DS(ON)} = 0.025~\Omega~$$
 @  $V_{GS} = 4.5~V.$ 

- Low gate charge.
- Fast switching speed.
- $\bullet$  High performance trench technology for extremely low  $R_{\scriptscriptstyle DS(ON)}.$



**TO-252** 

Absolute Maximum Ratings Tc=25°C unless otherwise noted



Symbol	Parameter	Ratings	Units	
$V_{DSS}$	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage		<u>±</u> 20	V
I <sub>D</sub>	Maximum Drain Current -Continuous	(Note 1)	35	А
		(Note 1a)	9	
	Maximum Drain Current -Pulsed		100	
P <sub>D</sub>	Maximum Power Dissipation @ T <sub>C</sub> = 25°C	(Note 1)	44	W
	$T_A = 25^{\circ}C$	(Note 1a)	2.8	
	$T_A = 25^{\circ}C$	(Note 1b)	1.3	
T <sub>J</sub> , T <sub>sta</sub>	Operating and Storage Junction Temperature	e Range	-55 to +150	°C

#### 

Package Marking and Ordering Information						
Device Marking	Device	Reel Size	Tape width	Quantity		
FDD6030BL	FDD6030BL	13"	16mm	2500		

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
055.01	IADA OTEDIOTICO					
BV <sub>DSS</sub>	ARACTERISTICS  Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	30		1	μA
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{DS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nΑ
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
00010	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	163 = 1, 153 1				117 (
	ARACTERISTICS (Note 2) Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1		3	V
ON CHA	ARACTERISTICS (Note 2)	, 10	1			
ON CHA	ARACTERISTICS (Note 2) Gate Threshold Voltage Static Drain-Source	$V_{DS} = V_{GS}, \ I_D = 250 \ \mu A$ $V_{GS} = 10 \ V, \ I_D = 9 \ A$ $V_{GS} = 4.5 \ V, \ I_D = 7.5 \ A$		<u> </u>	3 0.018	V
ON CHA	ARACTERISTICS (Note 2) Gate Threshold Voltage Static Drain-Source On-Resistance	$\begin{aligned} &V_{DS} = V_{GS}, \ I_D = 250 \ \mu A \\ &V_{GS} = 10 \ V, \ I_D = 9 \ A \\ &V_{GS} = 4.5 \ V, \ I_D = 7.5 \ A \end{aligned}$ RISTICS AND MAXIMUM F			3 0.018	V

#### Notes:

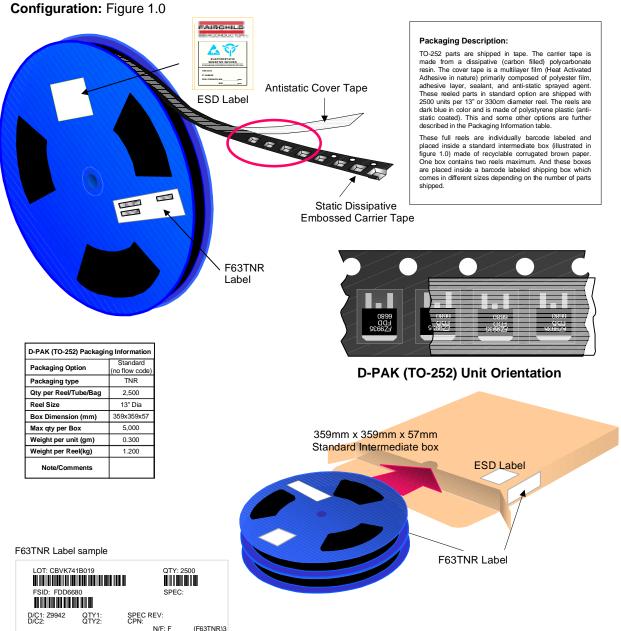
<sup>1.</sup>  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the drain tab.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



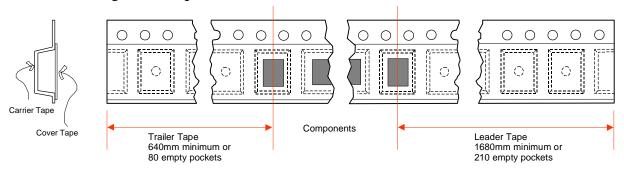
Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

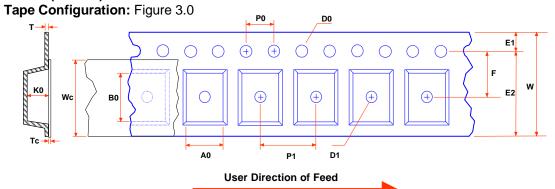
# D-PAK (TO-252) Packaging



# TO-252 (D-PAK) Tape Leader and Trailer Configuration: Figure 2.0



## D-PAK (TO-252) Embossed Carrier

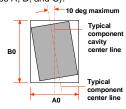


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>TO252</b> (24mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4.0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

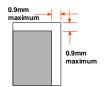
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

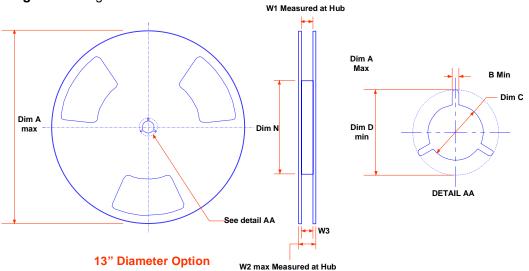


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

# D-PAK (TO-252) Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 - 0.764 15.9 - 19.4

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